

In the Claims

1. (Currently Amended) An organic electroluminescent device comprising:
a substrate;
a thin film transistor formed on the substrate;
a first electrode electrically coupled to the thin film transistor and having a surface treated by oxygen plasma;
a chemical vapor deposition insulating film formed on the first electrode and the substrate, the chemical vapor deposition film having an opening portion extending to ~~for exposing~~ the first electrode;
an organic electroluminescent layer formed in the opening portion; and
a second electrode formed on the organic electroluminescent layer.
2. (Previously Presented) The device as claimed in claim 1, wherein the chemical vapor deposition insulating film comprises SiOC.
3. (Previously Presented) The device as claimed in claim 1, wherein the chemical vapor deposition insulating film has a dielectric constant less than about 3.5.
4. (Previously Presented) The device as claimed in claim 1, wherein the chemical vapor deposition insulating film is formed to have a thickness more than about 1 μm between the first electrode and the organic electroluminescent layer.
- 5-9. (Canceled)
10. (Currently Amended) ~~An organic electroluminescent device comprising:
a substrate;
a first electrode formed on the substrate;
a chemical vapor deposition insulating film formed on the first electrode and the substrate;
the chemical vapor deposition insulating film having an opening portion formed on the first electrode with an inverse tapered shape;~~

~~an organic electroluminescent layer formed in the opening portion; and
a stripe-shaped second electrode formed on the organic electroluminescent layer, the
stripe-shaped second electrode being arranged to cross the first electrode~~

The device as claimed in claim 1, wherein the opening portion of the chemical vapor
deposition insulating film has a tapered shape, and the second electrode has a stripe shape and
crosses the first electrode.

11. (Previously Presented) The device as claimed in claim 10, wherein the chemical vapor deposition insulating film is comprised of SiOC.

12. (Previously Presented) The device as claimed in claim 10, wherein the chemical vapor deposition insulating film has a dielectric constant less than about 3.5.

13. (Previously Presented) The device as claimed in claim 10, wherein the chemical vapor deposition insulating film has a thickness more than about 1 μm between the first electrode and the organic electroluminescent layer.

14-16. (Canceled)